8-Bit Addressable Latch 1-of-8 Decoder

High-Performance Silicon-Gate CMOS

The MC54/74HC259 is identical in pinout to the LS259. The device inputs are compatible with standard CMOS outputs; with pullup resistors, they are compatible with LSTTL outputs.

The HC259 has four modes of operation as shown in the mode selection table. In the addressable latch mode, the data on Data In is written into the addressed latch. The addressed latch follows the data input with all non–addressed latches remaining in their previous states. In the memory mode, all latches remain in their previous state and are unaffected by the Data or Address inputs. In the one–of–eight decoding or demultiplexing mode, the addressed output follows the state of Data In with all other outputs in the LOW state. In the Reset mode all outputs are LOW and unaffected by the address and data inputs. When operating the HC259 as an addressable latch, changing more than one bit of the address could impose a transient wrong address. Therefore, this should only be done while in the memory mode.

• Output Drive Capability: 10 LSTTL Loads

Outputs Directly Interface to CMOS, NMOS, and TTL

Operating Voltage Range: 2 to 6 V

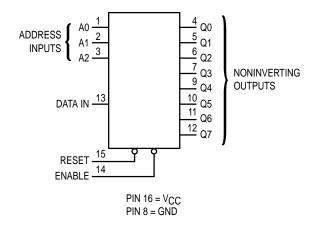
Low Input Current: 1 μA

High Noise Immunity Characteristic of CMOS Devices

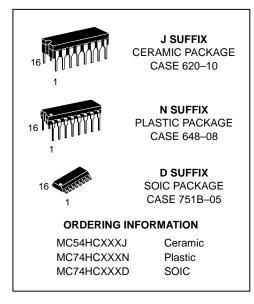
 In Compliance with the Requirements Defined by JEDEC Standard No. 7A

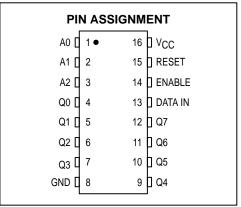
• Chip Complexity: 202 FETs or 50.5 Equivalent Gates

LOGIC DIAGRAM



MC54/74HC259





MODE SELECTION TABLE Enable Reset Mode L H Addressable Latch H H Memory L L 8-Line Demultiplexer H L Reset

LATCH SELECTION TABLE

Add	lress Inp	Latch	
С	В	Α	Addressed
L	L	L	Q0
L	L	Н	Q1
L	Н	L	Q2
L	Н	Н	Q3
Н	L	L	Q4
Н	L	Н	Q5
Н	Н	L	Q6
Н	Н	Н	Q7

MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	- 1.5 to V _{CC} + 1.5	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to V _{CC} + 0.5	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 25	mA
Icc	DC Supply Current, V _{CC} and GND Pins	± 50	mA
PD	Power Dissipation in Still Air, Plastic or Ceramic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds (Plastic DIP or SOIC Package) (Ceramic DIP)	260 300	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq VCC. Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or VCC).

Unused outputs must be left open.

Ceramic DIP: - 10 mW/°C from 100° to 125°C

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter			Max	Unit
VCC	DC Supply Voltage (Referenced to GND)			6.0	٧
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)			VCC	V
TA	Operating Temperature, All Package Types		- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time V (Figure 1) V	CC = 2.0 V CC = 4.5 V CC = 6.0 V	0 0 0	1000 500 400	ns

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Guaranteed Limit			
Symbol	Parameter	Test Conditions	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
V _{IH}	Minimum High–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.5 3.15 4.2	1.5 3.15 4.2	1.5 3.15 4.2	٧
V _{IL}	Maximum Low–Level Input Voltage	$V_{Out} = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $ I_{Out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.3 0.9 1.2	0.3 0.9 1.2	0.3 0.9 1.2	V
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} I_{\text{out}} \le 4.0 \text{ mA} \\ I_{\text{out}} \le 5.2 \text{ mA}$	4.5 6.0	3.98 5.48	3.84 5.34	3.70 5.20	
VOL	Maximum Low–Level Output Voltage	$V_{in} = V_{IH} \text{ or } V_{IL}$ $ I_{out} \le 20 \mu\text{A}$	2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		$V_{\text{in}} = V_{\text{IH}} \text{ or } V_{\text{IL}} I_{\text{out}} \le 4.0 \text{ mA} I_{\text{out}} \le 5.2 \text{ mA}$	4.5 6.0	0.26 0.26	0.33 0.33	0.40 0.40	
l _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND	6.0	± 0.1	± 1.0	± 1.0	μΑ
lcc	Maximum Quiescent Supply Current (per Package)	V _{in} = V _{CC} or GND I _{out} = 0 µA	6.0	8	80	160	μΑ

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

^{*} Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: - 10 mW/°C from 65° to 125°C

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

			Guaranteed Limit			
Symbol	Parameter	v _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Data to Output (Figures 1 and 6)	2.0 4.5 6.0	185 37 31	230 46 39	280 56 48	ns
tPLH, tPHL	Maximum Propagation Delay, Address Select to Output (Figures 2 and 6)	2.0 4.5 6.0	215 43 37	270 54 46	325 65 55	ns
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Enable to Output (Figures 3 and 6)	2.0 4.5 6.0	200 40 34	250 50 43	300 60 51	ns
[†] PHL	Maximum Propagation Delay, Reset to Output (Figures 4 and 6)	2.0 4.5 6.0	155 31 26	195 39 33	235 47 40	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 6)	2.0 4.5 6.0	75 15 13	95 19 16	110 22 19	ns
C _{in}	Maximum Input Capacitance	_	10	10	10	pF

NOTES:

- For propagation delays with loads other than 50 pF, see Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).
 Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance (Per Package)*	30	pF

^{*} Used to determine the no–load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see Chapter 2 of the Motorola High–Speed CMOS Data Book (DL129/D).

TIMING REQUIREMENTS (Input $t_r = t_f = 6 \text{ ns}$)

			Gu	Guaranteed Limit		
Symbol	Parameter	V _{CC}	– 55 to 25°C	≤ 85°C	≤ 125°C	Unit
t _{SU}	Minimum Setup Time, Address or Data to Enable (Figure 5)	2.0 4.5 6.0	100 20 17	125 25 21	150 30 26	ns
t _h	Minimum Hold Time, Enable to Address or Data (Figure 5)	2.0 4.5 6.0	5 5 5	5 5 5	5 5 5	ns
t _W	Minimum Pulse Width, Reset or Enable (Figure 3 or 4)	2.0 4.5 6.0	80 16 14	100 20 17	120 24 20	ns
t _r , t _f	Maximum Input Rise and Fall Times (Figure 1)	2.0 4.5 6.0	1000 500 400	1000 500 400	1000 500 400	ns

NOTE: Information on typical parametric values can be found in Chapter 2 of the Motorola High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS

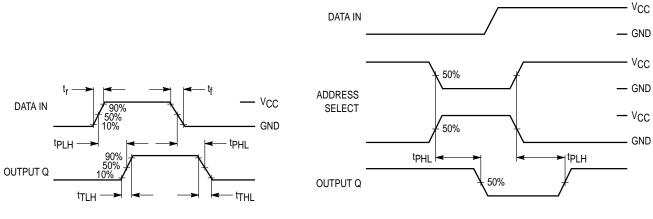


Figure 1.

Figure 2.

VCC

VCC

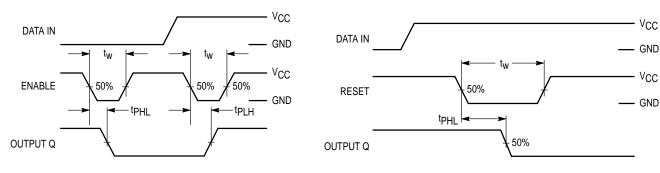


Figure 3.

Figure 4.

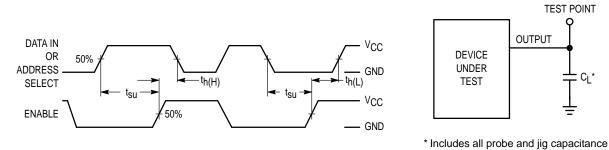
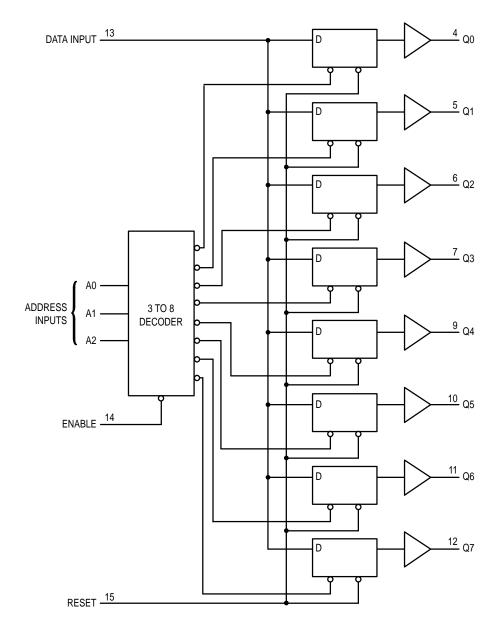


Figure 5.

Figure 6. Test Circuit

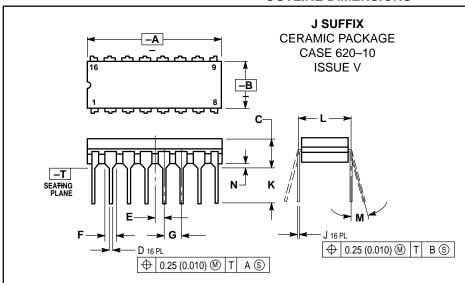
CL*

EXPANDED LOGIC DIAGRAM



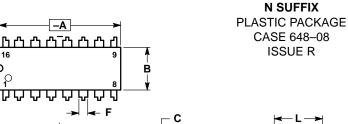
5

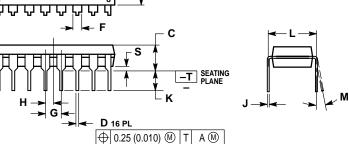
OUTLINE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEAD WHEN
 FORMED PARALLEL.
- 4. DIM F MAY NARROW TO 0.76 (0.030) WHERE THE LEAD ENTERS THE CERAMIC BODY.

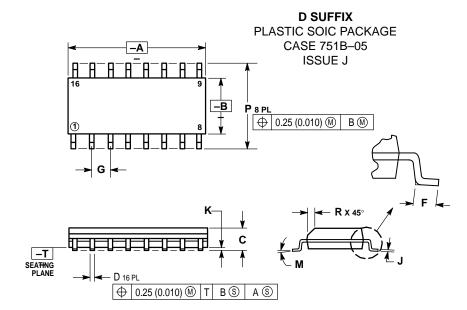
	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.750	0.785	19.05	19.93
В	0.240	0.295	6.10	7.49
С	_	0.200	_	5.08
D	0.015	0.020	0.39	0.50
E	0.050	BSC	1.27	BSC
F	0.055	0.065	1.40	1.65
G	0.100	BSC	2.54	BSC
J	0.008	0.015	0.21	0.38
K	0.125	0.170	3.18	4.31
L	0.300	BSC	7.62	BSC
M	0°	15°	0°	15°
N	0.020	0.040	0.51	1.01





- 1. DIMENSIONING AND TOLERANCING PER ANSI
- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. CONTROLLING DIMENSION: INCH. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL. DIMENSION B DOES NOT INCLUDE MOLD FLASH. ROUNDED CORNERS OPTIONAL.

	INC	HES	MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.740	0.770	18.80	19.55
В	0.250	0.270	6.35	6.85
С	0.145	0.175	3.69	4.44
D	0.015	0.021	0.39	0.53
F	0.040	0.070	1.02	1.77
G	0.	100 BSC	2	.54 BSC
Н	0.	050 BSC	1	.27 BSC
J	0.008	0.015	0.21	0.38
K	0.110	0.130	2.80	3.30
L	0.295	0.305	7.50	7.74
M	0°	10°	0°	10°
S	0.020	0.040	0.51	1.01



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

- T 14-30M, 1962.
 CONTROLLING DIMENSION: MILLIMETER.
 DIMENSIONS A AND B DO NOT INCLUDE
 MOLD PROTRUSION.
 MAXIMUM MOLD PROTRUSION 0.15 (0.006)
- MAXIMUM MOLD PROTRUSION 0.15 (0.006)
 PER SIDE.
 DIMENSION D DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE DAMBAR
 PROTRUSION SHALL BE 0.127 (0.005) TOTAL
 IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	9.80	10.00	0.386	0.393
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.2	7 BSC	0.050) BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
Р	5.80	6.20	0.229	0.244
R	0.25	0.50	0.010	0.019

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